

**40A Low Barrier Diode** 

### ■ Features

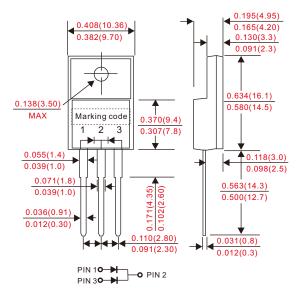
- · Low forward voltage drop.
- Excellent high temperature stability.
- Fast switching capability.
- Suffix "G" indicates Halogen-free part, ex.CSF40L100CTG-A.
- Lead-free parts meet environmental standards of MIL-STD-19500 /228

### ■ Mechanical data

- Epoxy: UL94-V0 rated flame retardant.
- Case: JEDEC ITO-220AB molded plastic body.
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026.
- Polarity: As marked.Mounting Position : Any.
- Weight: Approximated 2.25 gram.

#### Outline

#### ITO-220AB



Dimensions in inches and (millimeters)

## ■ Maximum ratings and electrical characteristics

Rating at  $25^{\circ}$ C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Conditions	Symbol	CSF40L100CT-A	UNIT
Marking code			CSF40L100CT	
Peak repetitive reverse voltage		V <sub>RRM</sub>		
Working peak reverse voltage		V <sub>RWM</sub>	100	V
DC blocking voltage		V <sub>RM</sub>		
Forward rectified current (total device)		I <sub>o</sub>	40	А
Forward surge current (per diode)	8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I <sub>FSM</sub>	280	А
Peak repetitive reverse surge current (per diode)	2us - 1kHz	I <sub>RRM</sub>	1	А
Thermal resistance(1) (per diode)	Junction to case	R <sub>eJC</sub>	4	°C/W
Operating and Storage temperature		T <sub>J</sub> , T <sub>STG</sub>	-65 ~ +175	°C

Parameter	Conditions	Symbol	MIN.	TYP.	MAX.	UNIT
Forward voltage drop (per diode)	$I_F = 20A, T_J = 25^{\circ}C$	V <sub>F</sub>			800	mV
	$I_F = 20A, T_J = 125^{\circ}C$				700	
I Reverse current (per diode)	$V_R = V_{RRM} T_J = 25^{\circ}C$	- I <sub>R</sub>			0.2	mA
	$V_R = V_{RRM} T_J = 125^{\circ}C$				30	

 $Note: 1. Thermal\ resistance\ from\ junction\ to\ case\ per\ leg,\ with\ heatsink\ size (1.35"\ x\ 0.95"\ x\ 0.18")\ Al-plate.$ 

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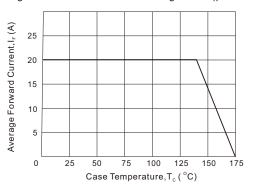
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# ■ Rating and characteristic curves

Fig.1 - Forward Current Derating Curve (per diode)



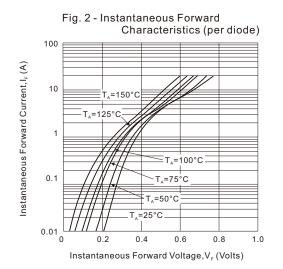
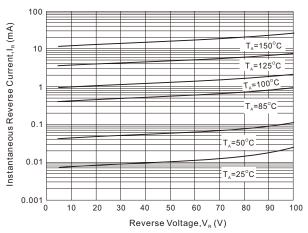


Fig. 3 - Reverse Characteristics (per diode)



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